NSN 5961-01-211-4738

Semiconductor Device Set - Page 1 of 1



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Inclosure Material:
Metal and ceramic all transistor
Overall Length:
0.960 inches and 0.980 inches all transistor
Overall Height:
0.229 inches and 0.290 inches all transistor
Mounting Facility Quantity:
2 all transistor
Internal Configuration:
Junction contact all transistor
Internal Junction Configuration:
Npn all transistor
Component Function Relationship:
Matched
Component Name And Quantity:
2 transistor
Mounting Method:
Unthreaded hole all transistor
Features Provided:
Hermetically sealed case
Semiconductor Material:
Silicon all transistor
Voltage Rating In Volts Per Characteristic:
35.0 collector to emitter voltage/static/base open and 65.0 collector to emitter voltage, dc with base short-circuited to emitter and 4.0
emitter to base voltage, static, collector open all transistor
Current Rating Per Characteristic:
20.00 amperes collector current, dc all transistor
Power Rating Per Characteristic:
320.0 watts total device dissipation all transistor
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius junction all transistor
Terminal Type And Quantity:
4 ribbon all transistor
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
Yes - demil/mli

Fiig:

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